

MOSFET - Power, Single N-Channel, DUAL COOL®, DFN8 5x6.15 80 V, 2.9 mΩ, 154 A

NTMFSC2D9N08H

Features

- Advanced Dual-Side Cooled Packaging
- Ultra Low $R_{DS(on)}$ to Minimize Conduction Losses
- MSL1 Robust Packaging Design
- Low Q_g and Q_{oss} to Minimize Charge Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- DC-DC Conversion
- O-ring FET/Load Switching
- Synchronous Rectification

MAXIMUM RATINGS (T_J = 25°C, Unless otherwise specified)

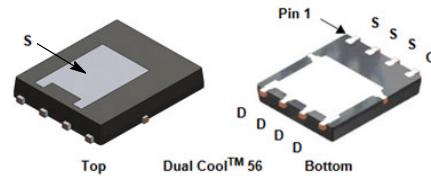
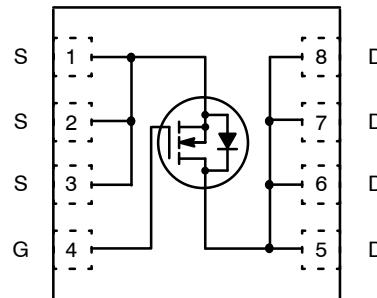
Parameter		Symbol	Value	Unit
Drain-to-Source Breakdown Voltage		V _{(BR)DSS}	80	V
Gate-to-Source Voltage		V _{GS}	±20	V
Continuous Drain Current R _{θJC} (Note 2)	Steady State	I _D	154	A
		P _D	166	W
Continuous Drain Current R _{θJA} (Note 1, 2)	Steady State	I _D	23	A
		P _D	3.8	W
Pulsed Drain Current	T _A = 25°C, t _p = 100 μs	I _{DM}	638	A
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C
Source Current (Body Diode)		I _S	138	A
Single Pulse Drain-to-Source Avalanche Energy (I _{AV} = 34 A)		E _{AS}	173	mJ
Lead Temperature Soldering Reflow for Soldering Purposes (1/8" from case for 10 s)		T _L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface-mounted on FR4 board using 1 in² pad size, 1 oz Cu pad.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

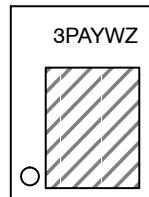
V _{(BR)DSS}	R _{DS(ON) MAX}	I _{D MAX}
80 V	2.9 mΩ @ 10 V	154 A

N-Channel MOSFET



DFN8 5x6.15
CASE 506EG

MARKING DIAGRAM



- 3P = Specific Device Code
 A = Assembly Location
 Y = Year
 W = Work Week
 Z = Assembly Lot Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

THERMAL CHARACTERISTICS

Symbol	Parameter	Max	Unit
$R_{\theta JC}$	Junction-to-Case – Steady State (Note 2)	0.9	°C/W
$R_{\theta JT}$	Junction-to-Top Source – Steady State (Note 2)	1.4	
$R_{\theta JA}$	Junction-to-Ambient – Steady State (Note 2)	39	

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0 \text{ V}, I_D = 250 \mu\text{A}$	80			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(\text{BR})\text{DSS}} / T_J$			58		$\text{mV}/^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{GS}} = 0 \text{ V}, V_{\text{DS}} = 80 \text{ V}$	$T_J = 25^\circ\text{C}$		10	μA
			$T_J = 125^\circ\text{C}$		100	
Gate-to-Source Leakage Current	I_{GSS}	$V_{\text{DS}} = 0 \text{ V}, V_{\text{GS}} = 20 \text{ V}$			100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{\text{GS}(\text{TH})}$	$V_{\text{GS}} = V_{\text{DS}}, I_D = 250 \mu\text{A}$	2.0		4.0	V
Negative Threshold Temperature Coefficient	$V_{\text{GS}(\text{TH})} / T_J$	$I_D = 250 \mu\text{A}$, ref to 25°C		-7.3		$\text{mV}/^\circ\text{C}$
Drain-to-Source On Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10 \text{ V}, I_D = 50 \text{ A}$		2.2	2.9	$\text{m}\Omega$
		$V_{\text{GS}} = 6 \text{ V}, I_D = 25 \text{ A}$		3.1	4.4	
Forward Trans-conductance	g_{FS}	$V_{\text{DS}} = 15 \text{ V}, I_D = 50 \text{ A}$		294		S
Gate-Resistance	R_G	$V_{\text{GS}} = 0 \text{ V}, f = 1 \text{ MHz}$		1	2.6	Ω

CHARGES & CAPACITANCES

Input Capacitance	C_{ISS}	$V_{\text{GS}} = 0 \text{ V}, f = 1 \text{ MHz}, V_{\text{DS}} = 40 \text{ V}$		4380		pF
Output Capacitance	C_{OSS}			610		
Reverse Transfer Capacitance	C_{RSS}			16		
Total Gate Charge	$Q_{\text{G}(\text{TOT})}$	$V_{\text{GS}} = 10 \text{ V}, V_{\text{DS}} = 40 \text{ V}, I_D = 50 \text{ A}$		68		nC
Threshold Gate Charge	$Q_{\text{G}(\text{TH})}$			11.8		
Gate-to-Source Charge	Q_{GS}			19		
Gate-to-Drain Charge	Q_{GD}			15		
Output Charge	Q_{OSS}		$V_{\text{DD}} = 40 \text{ V}, V_{\text{GS}} = 0 \text{ V}$	108		nC

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	$t_{\text{d}(\text{ON})}$	$V_{\text{GS}} = 10 \text{ V}, V_{\text{DS}} = 40 \text{ V}, I_D = 50 \text{ A}, R_G = 2.5 \Omega$		20.5		ns
Rise Time	t_r			14		
Turn-Off Delay Time	$t_{\text{d}(\text{OFF})}$			42		
Fall Time	t_f			9.5		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{\text{GS}} = 0 \text{ V}, I_S = 50 \text{ A}$	$T_J = 25^\circ\text{C}$		0.80	1.2	V
			$T_J = 150^\circ\text{C}$		0.65		
Reverse Recovery Time	t_{RR}	$V_{\text{GS}} = 0 \text{ V}, dI_S/dt = 100 \text{ A}/\mu\text{s}, I_S = 50 \text{ A}$			64		ns
					81		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

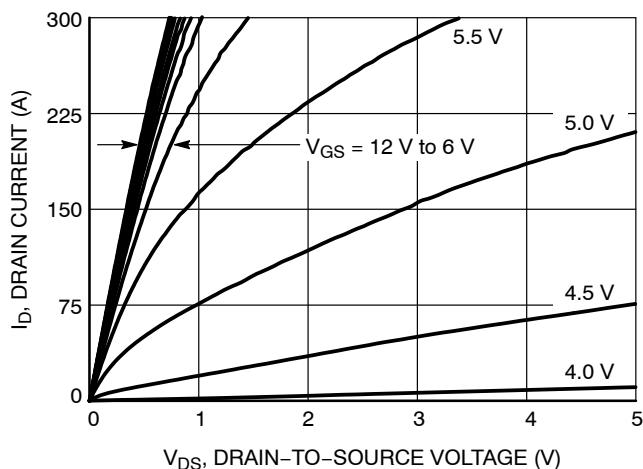


Figure 1. On-Region Characteristics

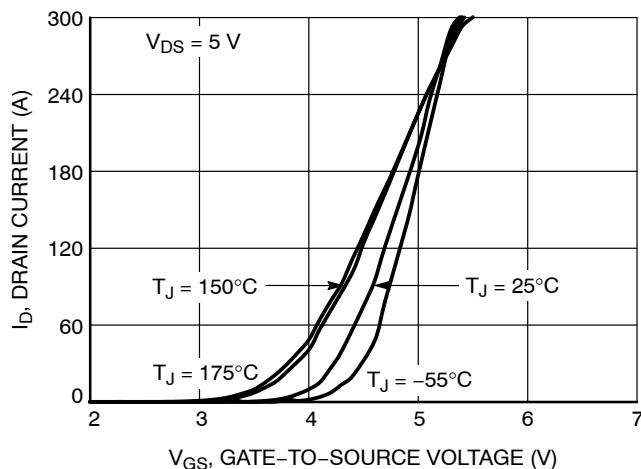


Figure 2. Transfer Characteristics

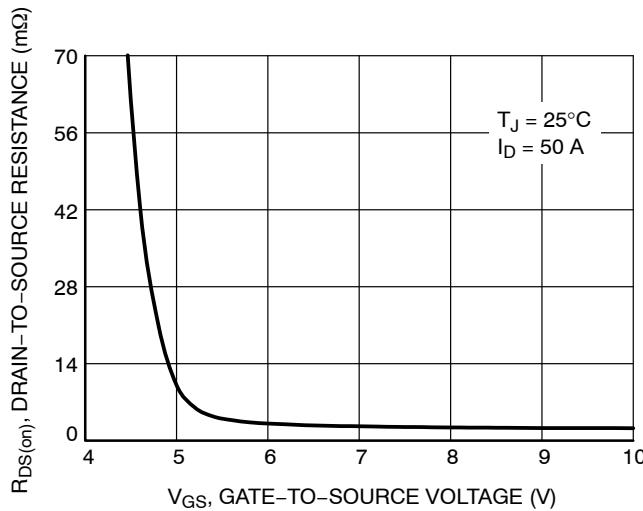


Figure 3. On-Resistance vs. Gate-to-Source Voltage

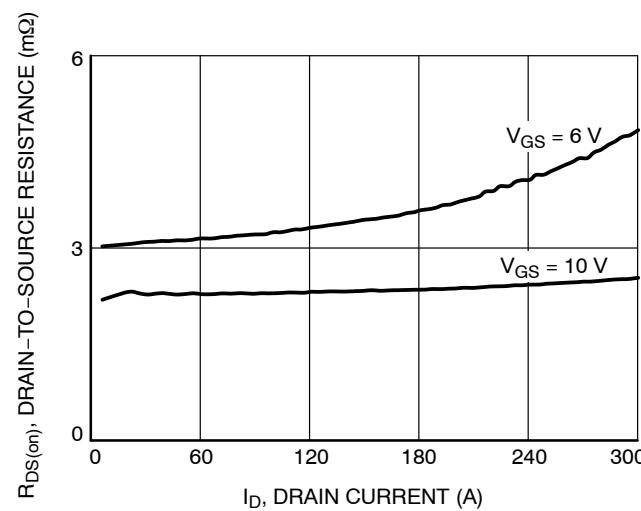


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

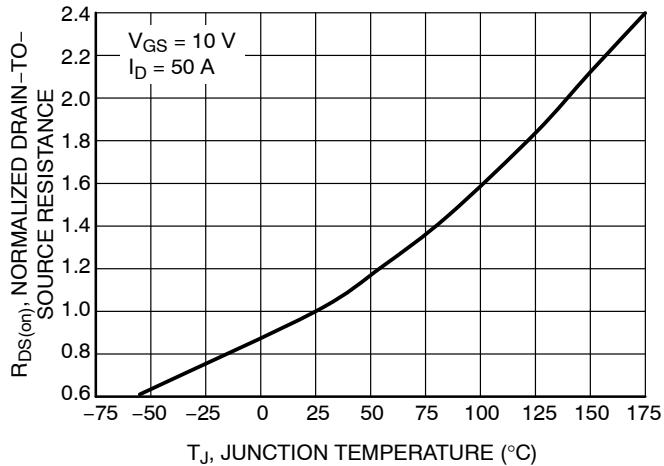


Figure 5. On-Resistance Variation with Temperature

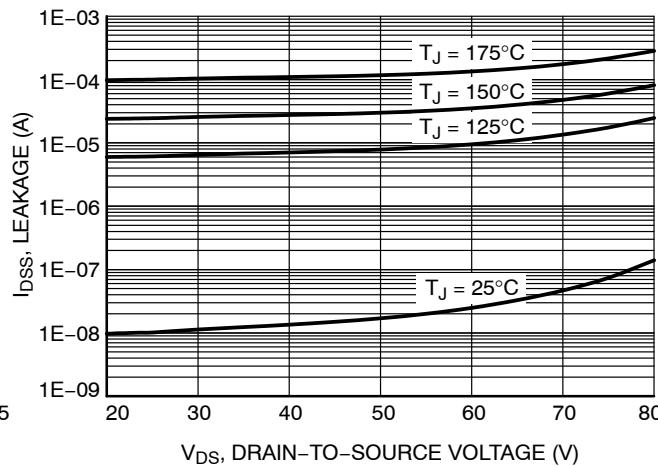


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

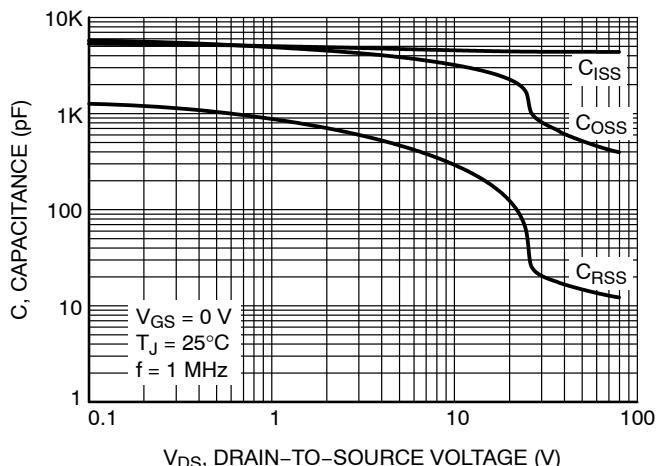


Figure 7. Capacitance Variation

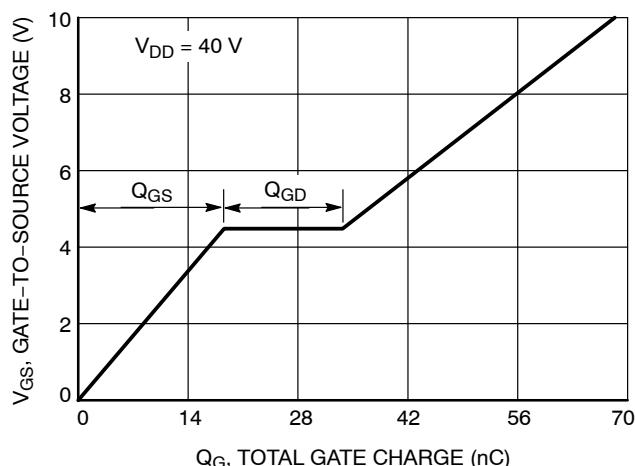


Figure 8. Gate-to-Source Voltage vs. Total Charge

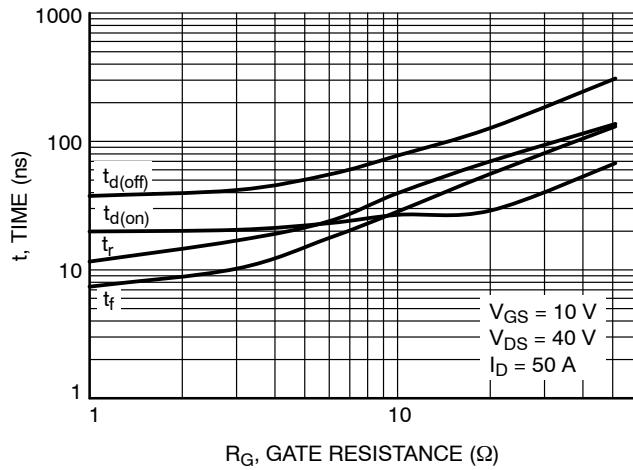


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

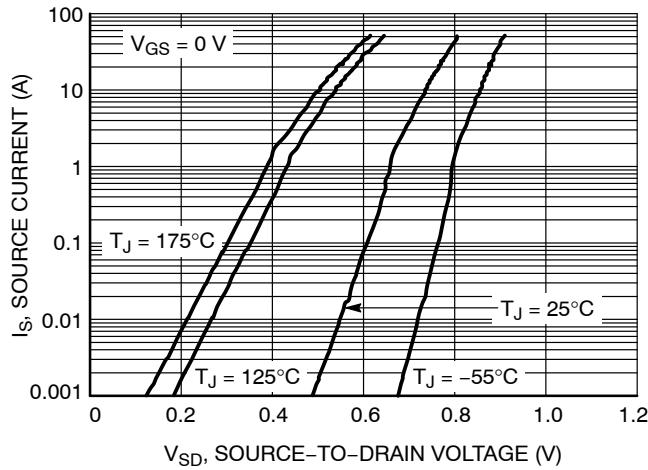


Figure 10. Diode Forward Voltage vs. Current

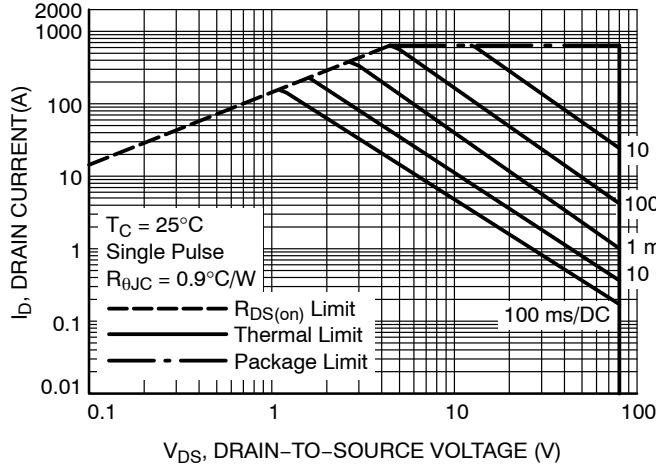


Figure 11. Forward Bias Safe Operating Area

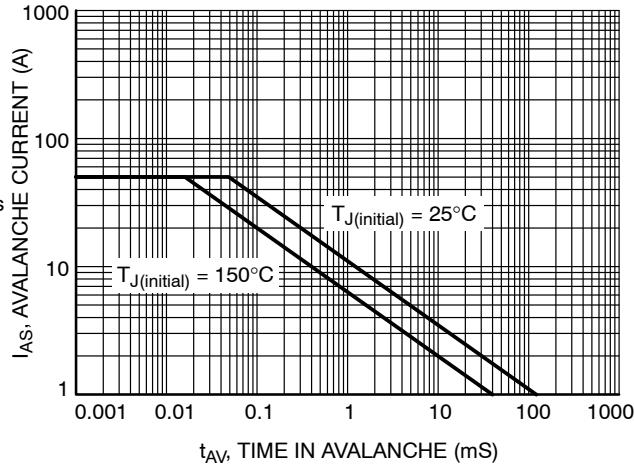


Figure 12. Unclamped Inductive Switching Capability

TYPICAL CHARACTERISTICS

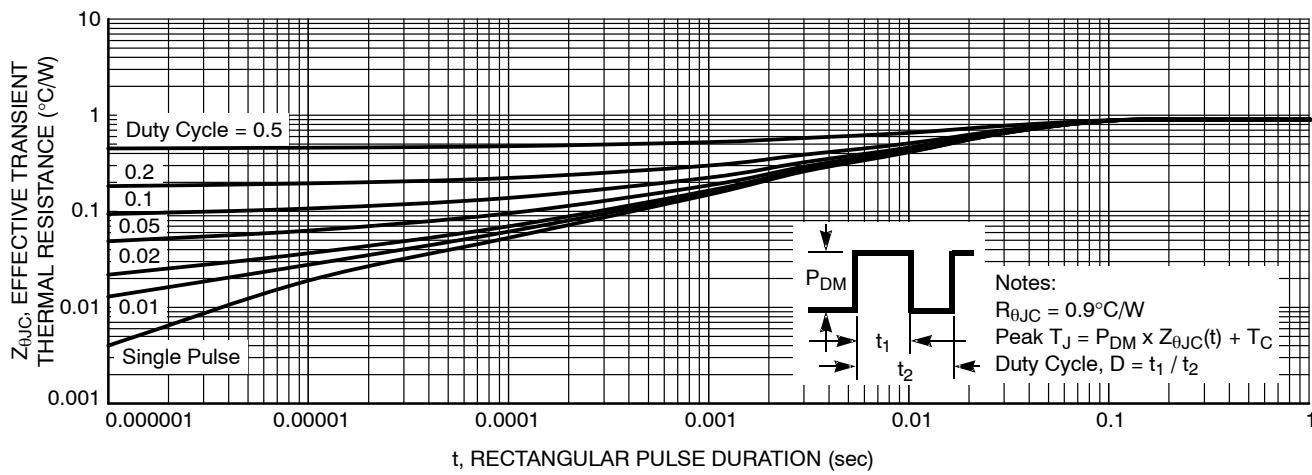


Figure 13. Transient Thermal Impedance

ORDERING INFORMATION

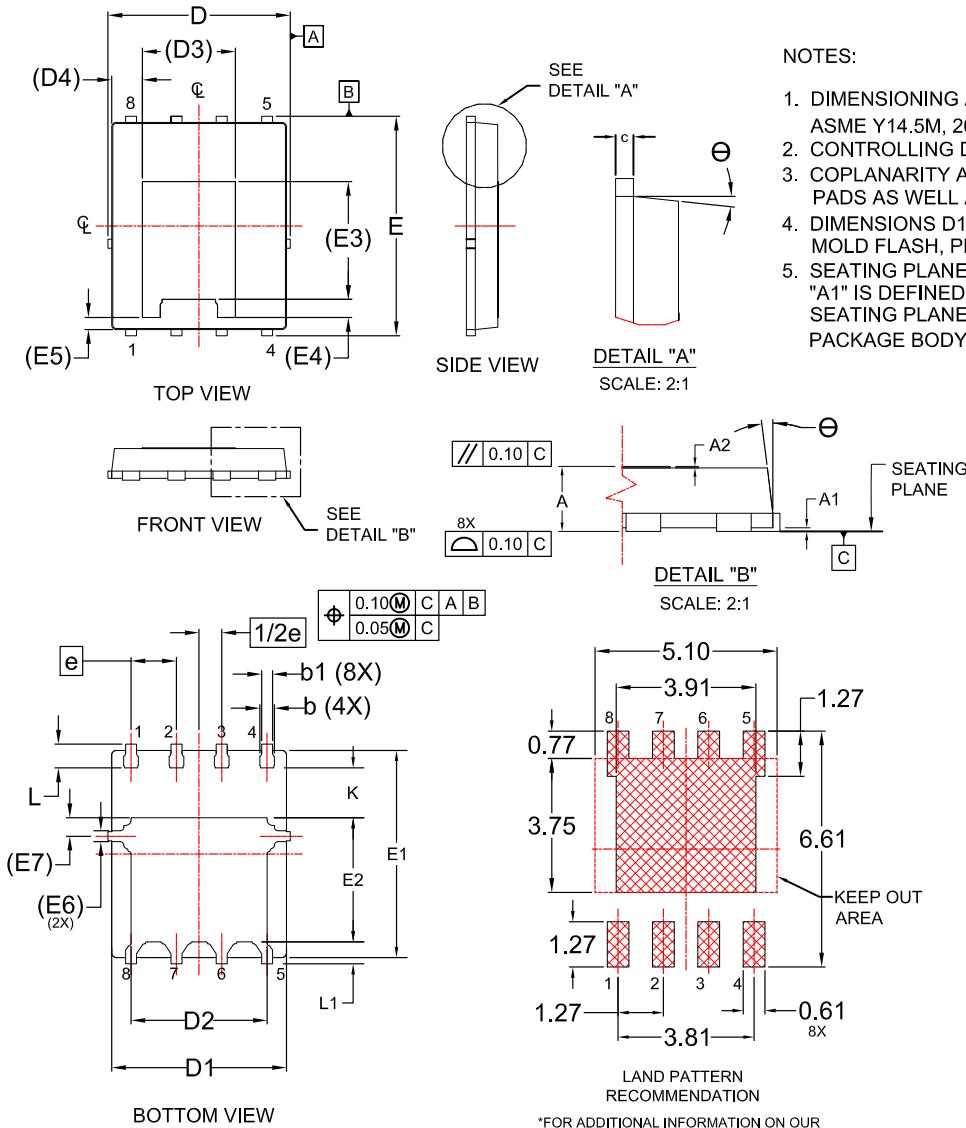
Device	Device Marking	Package	Shipping [†]
NTMFSC2D9N08H	2D9N08	DFN8 (Pb-Free/Halogen Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



DFN8 5x6.15, 1.27P, DUAL COOL
CASE 506EG
ISSUE D

DATE 25 AUG 2020



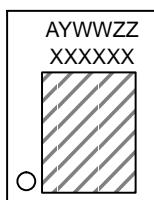
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
4. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
5. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.85	0.90	0.95
A1	-	-	0.05
A2	-	-	0.05
b	0.31	0.41	0.51
b1	0.21	0.31	0.41
c	0.20	0.25	0.30
D	4.90	5.00	5.10
D1	4.80	4.90	5.00
D2	3.67	3.82	3.97
D3	2.60 REF		
D4	0.86 REF		
E	6.05	6.15	6.25
E1	5.70	5.80	5.90
E2	3.38	3.48	3.58
E3	3.30 REF		
E4	0.50 REF		
E5	0.34 REF		
E6	0.30 REF		
E7	0.52 REF		
e	1.27 BSC		
1/2e	0.635 BSC		
K	1.30	1.40	1.50
L	0.56	0.66	0.76
L1	0.52	0.62	0.72
Θ	0°	---	12°

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SODERRM/D.

**GENERIC
MARKING DIAGRAM***



XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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